

CZT651

SURFACE MOUNT
NPN HIGH CURRENT TRANSISTOR



SOT-223 CASE

CentralTM
Semiconductor Corp.

DESCRIPTION:

The CENTRAL SEMICONDUCTOR CZT651 type is a NPN Silicon Transistor manufactured by the epitaxial planar process, epoxy molded in a surface mount package, designed for high current applications

MAXIMUM RATINGS: ($T_A=25^{\circ}\text{C}$)

			UNITS
Collector-Base Voltage	V_{CBO}	80	V
Collector-Emitter Voltage	V_{CEO}	60	V
Emitter-Base Voltage	V_{EBO}	5.0	V
Collector Current	I_C	2.0	A
Power Dissipation	P_D	2.0	W
Operating and Storage			
Junction Temperature	T_J, T_{stg}	-65 to +150	$^{\circ}\text{C}$
Thermal Resistance	θ_{JA}	62.5	$^{\circ}\text{C/W}$

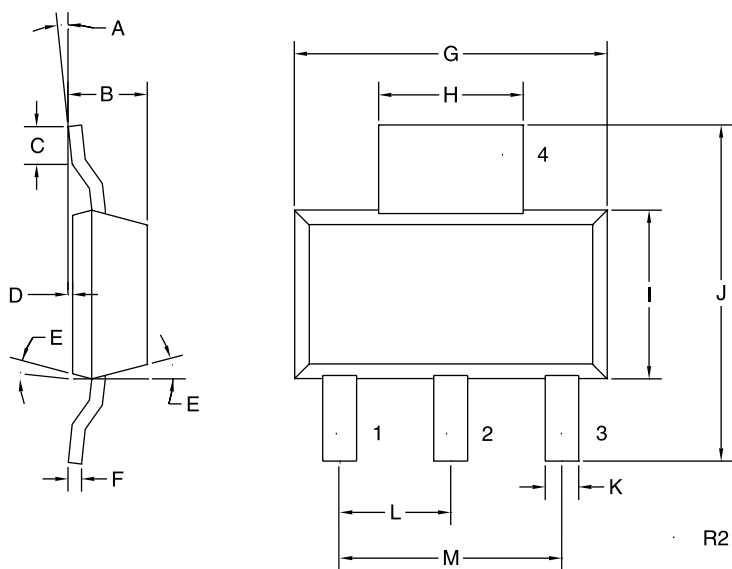
ELECTRICAL CHARACTERISTICS: ($T_A=25^{\circ}\text{C}$ unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	MAX	UNITS
I_{CBO}	$V_{CB}=80\text{V}$		100	nA
I_{EBO}	$V_{EB}=4.0\text{V}$		100	nA
BV_{CBO}	$I_C=100\mu\text{A}$	80		V
BV_{CEO}	$I_C=10\text{mA}$	60		V
BV_{EBO}	$I_E=10\mu\text{A}$	5.0		V
$V_{CE(SAT)}$	$I_C=1.0\text{A}, I_B=100\text{mA}$		0.3	V
$V_{CE(SAT)}$	$I_C=2.0\text{A}, I_B=200\text{mA}$		0.5	V
$V_{BE(SAT)}$	$I_C=1.0\text{A}, I_B=100\text{mA}$		1.2	V
$V_{BE(ON)}$	$V_{CE}=2.0\text{V}, I_C=1.0\text{A}$		1.0	V
h_{FE}	$V_{CE}=2.0\text{V}, I_C=50\text{mA}$	75		
h_{FE}	$V_{CE}=2.0\text{V}, I_C=500\text{mA}$	75		
h_{FE}	$V_{CE}=2.0\text{V}, I_C=1.0\text{A}$	75		
h_{FE}	$V_{CE}=2.0\text{V}, I_C=2.0\text{A}$	40		
f_T	$V_{CE}=5.0\text{V}, I_C=50\text{mA}, f=100\text{MHz}$	75		MHz

R1 (01-Feb 2001)

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TRANSISTOR**

SOT-223 CASE - MECHANICAL OUTLINE



LEAD CODE:

- 1) BASE
- 2) COLLECTOR
- 3) EMITTER
- 4) COLLECTOR

DIMENSIONS				
SYMBOL	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0°	7°	0°	7°
B	0.063	0.067	1.60	1.70
C	0.022		0.55	
D	0.001	0.004	0.03	0.10
E	15°		15°	
F	0.009	0.013	0.23	0.33
G	0.248	0.264	6.30	6.71
H	0.114	0.122	2.90	3.10
I	0.130	0.146	3.30	3.71
J	0.264	0.287	6.71	7.29
K	0.024	0.031	0.61	0.79
L	0.091		2.31	
M	0.181		4.60	

SOT-223 (REV: R2)

R1 (01-Feb 2001)